

SLVSCD1B-DECEMBER 2013-REVISED JANUARY 2014

# TPS92561 – Phase Dimmable, Single Stage Boost Controller for LED Lighting

## **FEATURES**

- Simple Hysteretic Control
- Compact Solution and Simple Bill Of Materials
- Naturally Dimmable TRIAC and Reverse Phase Dimmers
- Implements LED Drive Circuits Capable of High >90% Efficiency, >0.9 Power Factor, and <20% THD</li>
- Programmable Output Over-voltage Protection
- Overtemperature Shutdown
- VCC Undervoltage Lockout
- 8-Pin VSSOP (MSOP) With Exposed Pad

### **APPLICATIONS**

- Off-Line TRIAC Dimmable Applications
- Off-Line Non-Dimmable Lamps
- Lamps Requiring the Highest Efficiency and Lowest BOM Cost
- Industrial and Commercial Solid State Lighting

### DESCRIPTION

The TPS92561 device is a boost controller for LED lighting applications utilizing high-voltage, low-current LEDs. A boost converter approach to lighting applications allows the creation of the smallest volume converter possible and enables high efficiencies beyond 90%. The device incorporates a current sense comparator with a fixed offset enabling a simple hysteretic control scheme free of the loop compensation issues typically associated with a boost converter. The integrated OVP and VCC regulator further simplify the design procedure and reduce external component count.

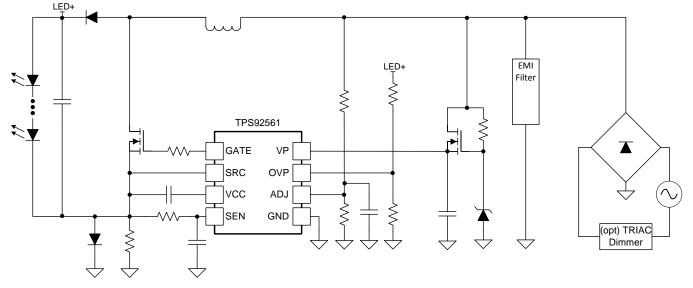


Figure 1. Typical Application Schematic

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## TPS92561

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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## Absolute Maximum Ratings<sup>(1)</sup>

Over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
	SRC, SEN, ADJ, OVP	-0.3	5.0	
Pin voltage range <sup>(2)</sup>	VP	-1.0	45.0	V
	VCC	-0.3	12.0	
ESD rating <sup>(3)</sup>	Human body model (HBM)	1.5		kV
T <sub>stg</sub>	Storage temperature range	-60	150	°C
TJ	Junction temperature range	Internally Limited		

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to network ground terminal.

(3) ESD testing is performed according to the respective JESD22 JEDEC standard.

### **Thermal Characteristics**

Over operating free-air temperature range (unless otherwise noted)

		TPS92561	
THERMAL METRIC <sup>(1)</sup>		DGN (8 PINS)	UNITS
$\theta_{JA}$	Junction-to-ambient thermal resistance <sup>(2)</sup>	65.3	
θ <sub>JCtop</sub>	Junction-to-case (top) thermal resistance <sup>(3)</sup>	64.8	
θ <sub>JB</sub>	Junction-to-board thermal resistance <sup>(4)</sup>	44.8	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter <sup>(5)</sup>	3.9	°C/VV
Ψјв	Junction-to-board characterization parameter <sup>(6)</sup>	44.6	
θ <sub>JCbot</sub>	Junction-to-case (bottom) thermal resistance <sup>(7)</sup>	13.2	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

(2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.

(3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specified JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.

(5) The junction-to-top characterization parameter,  $\theta_{JT}$ , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining  $\theta_{JA}$ , using a procedure described in JESD51-2a (sections 6 and 7).

(6) The junction-to-board characterization parameter,  $\theta_{JB}$ , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining  $\theta_{JA}$ , using a procedure described in JESD51-2a (sections 6 and 7).

(7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

### **Recommended Operating Conditions**

Over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
VP	Supply voltage	6.5	42	V
TJ	Operating junction temperature	-40	125	°C



### **Electrical Characteristics**

Over recommended operating conditions with –40°C  $\leq$   $T_{\rm J}$   $\leq$  125°C. VCC = 12 V.  $C_{\rm VCC}$  = 0.47  $\mu F$ 

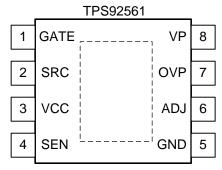
PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT	
SUPPLY							
I <sub>IN</sub>	V <sub>P</sub> operating current	6.5 V < V <sub>VP</sub> < 42 V	0.5	1.0	1.6	mA	
VCC Regulator							
		$ I_{CC} \le 10 \text{ mA}  C_{VCC} = 0.47 \mu\text{F}  12 V < V_{VP} < 42 V $	7.75	8.35	8.95		
VCC	V <sub>CC</sub> regulated voltage		5.42	5.92	6.42	V	
		$    I_{CC} = 0 \mbox{ mA} \\ C_{VCC} = 0.47  \mu F \\ V_{VP} = 2  V $		2			
I <sub>CC-LIM</sub>	V <sub>CC</sub> current limit	V <sub>CC</sub> = 0 V 6.5 V < V <sub>VP</sub> < 42 V	20	34	56	mA	
V <sub>CC-UVLO-UPTH</sub>	V <sub>CC</sub> UVLO rising threshold		5.00	5.44	5.85	V	
V <sub>CC-UVLO-LOTH</sub>	V <sub>CC</sub> UVLO falling threshold		4.68	5.07	5.46	V	
MOSFET Gate	Driver						
V <sub>GATE-HIGH</sub>	Gate driver output high	With respect to SRC Sinking 100 mA from GATE Force VCC = 9.5 V	8.00	8.71	9.41	V	
V <sub>GATE-LOW</sub>	Gate driver output low	With respect to SRC Sourcing 100 mA to GATE	10	180	350	mV	
t <sub>RISE</sub>	V <sub>GATE</sub> rise time	C <sub>GATE</sub> = 1 nF across GATE and SRC		37			
t <sub>FALL</sub>	V <sub>GATE</sub> fall time	C <sub>GATE</sub> = 1 nF across GATE and SRC		30			
t <sub>RISE-PG-DELAY</sub>	V <sub>GATE</sub> low-to-high propagation delay	$C_{GATE} = 1 \text{ nF}$ across GATE and SRC		91		ns	
t <sub>FALL-PG-DELAY</sub>	V <sub>GATE</sub> high-to-low propagation delay	C <sub>GATE</sub> = 1 nF across GATE and SRC		112			
Current Source	e at ADJ Pin	•	1				
IADJ-STARTUP	Output current of ADJ pin at start-up	V <sub>ADJ</sub> < 90 mV	14	20	26	μA	
<b>Current Sense</b>	Amplifier		L.				
V <sub>SEN-UPPER-TH</sub>	$V_{\mbox{\scriptsize SEN}}$ upper threshold over $V_{\mbox{\scriptsize ADJ}}$	$V_{SEN} - V_{ADJ}$ $V_{ADJ} = 0.2 V$ $V_{GATE}$ at falling edge	17.6	29.3	41		
V <sub>SEN-LOWER</sub> -TH	$V_{\mbox{\scriptsize SEN}}$ lower threshold over $V_{\mbox{\scriptsize ADJ}}$	$V_{SEN} - V_{ADJ}$ $V_{ADJ} = 0.2 V$ $V_{GATE}$ at rising edge	-40.7	-29.1	-17.5	mV	
V <sub>SEN-HYS</sub>	V <sub>SEN</sub> hysteresis	(V <sub>SEN-UPPER-TH</sub> – V <sub>SEN-LOWER-TH</sub> )	40.9	60.0	75.9		
V <sub>SEN-OFFSET</sub>	$V_{SEN}$ offset with respect to $V_{ADJ}$	(V <sub>SEN-UPPER-TH</sub> + V <sub>SEN-LOWER-TH</sub> ) / 2	-4.0	-0.1	4.0		
	Itage Protection (OVP)	·	·				
V <sub>OVP-UPTH</sub>	Output overvoltage detection upper threshold	$V_{\text{OVP}}$ increasing, $V_{\text{GATE}}$ at falling edge	1.11	1.19	1.27	V	
V <sub>OVP-HYS</sub>	Output overvoltage detection hysteresis	V <sub>OVP-UPTH</sub> – V <sub>OVP-LOTH</sub>	15	44	80	mV	
Thermal Shutd	own		·				
T <sub>SD</sub>	Thermal shutdown temperature	T <sub>J</sub> rising		165		•••	
T <sub>SD-HYS</sub>	Thermal shutdown temperature hysteresis	T <sub>.1</sub> falling		30		°C	

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### **DEVICE INFORMATION**

### 8-PIN VSSOP (MSOP) PACKAGE (EXPOSED PAD) (TOP VIEW)



### Table 1. Terminal Functions

PIN		DEGODIDITION	
NAME	NO.	DESCRIPTION	APPLICATION INFORMATION
GATE	1	Gate driver output pin	Connect to the gate terminal of the low-side N-channel power FET. For off-line applications, use a gate resistance of $\geq$ 75 $\Omega$ .
SRC	2	Gate driver return	Connect to the source terminal of the low-side, N-channel power FET. By connecting SRC to the FET source, switching current spikes are not passed through the sense resistor.
VCC	3	Gate driver power rail	Connect a 0.47-µF minimum decoupling cap from this pin to SRC pin.
SEN	4	LED current sense pin	Current sense input. For off-line applications, connect to SEN and the current sensing resistor through an R-C filter with a time constant similar to the converter switching frequency.
GND	5	Ground	Connect to the system ground plane.
ADJ	6	LED current adjust pin	Converter reference. Can be connected to the converter rectified AC for high power factor, or to the LED output voltage for improved line regulation.
OVP	7	Overvoltage	Connect to resistor divider from VOUT (LED+) to detect overvoltage.
VP	8	Power supply of the integrated circuit (IC)	Connect to an appropriate voltage source to provide power for the IC. (VP $\leq$ 42 V) See Application Circuits for example diagrams.
PowerPAD			Solder to printed circuit board (PCB) with or without thermal vias to enhance thermal performance. Although it can be left floating, TI recommends to connect the PowerPAD <sup>™</sup> to GND.



## **Block Diagram**

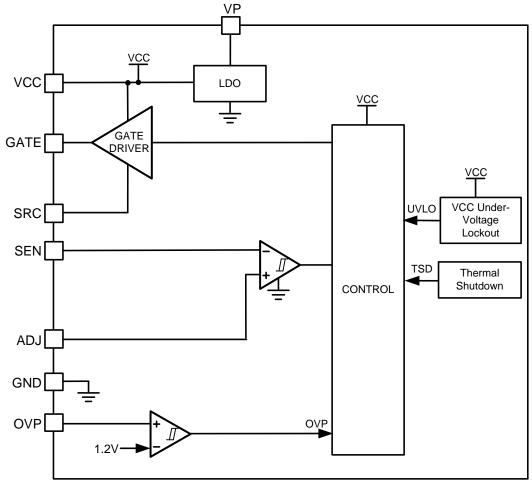


Figure 2. Functional Block Diagram



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### **Typical Characteristics**

 $V_P = V_{P_NOM} = 12 V$ 

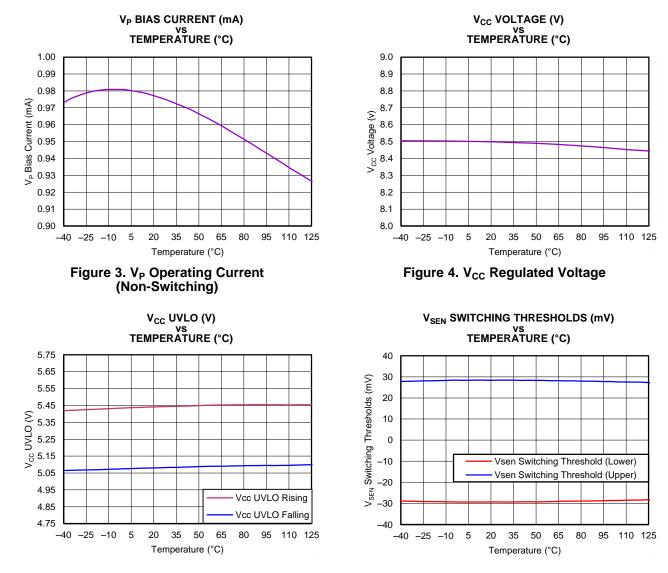
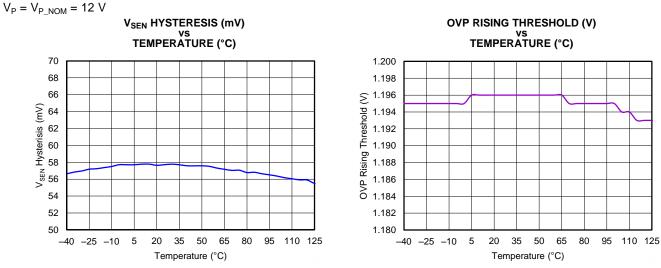


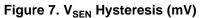
Figure 5. V<sub>CC</sub> UVLO Thresholds

Figure 6.  $V_{SEN}$  Switching Thresholds (mV)













### **APPLICATION INFORMATION**

### Description

The TPS92561 device is a boost controller for phase cut dimmer compatible LED lighting applications. The device incorporates a current sense comparator with a fixed offset, allowing the construction of a hysteretic, off-line converter suitable for driving LEDs in a wide variety of applications.

The inductor peak-to-peak current ripple follows the device reference, the ADJ pin voltage ( $V_{ADJ}$ ), and is bounded by the SEN pin hysteresis ( $V_{SEN-HYS}$ ). By using a voltage divider from the rectified AC voltage, the inductor current can be made to follow the line closely and create conversions which result in high power factor and low THD. Boost converters also have an advantage when TRIAC dimming because of their inherent ability to draw continuous current from the line. This eliminates the need for additional hold current circuitry as the converter itself can draw power until the zero crossing point is reached. The continuous input current of a boost also reduces the input EMI filter requirements.

### **Basics of Operation**

The main switch is turned on and off when the SEN comparator reaches trip points in a window around the ADJ reference. In cycle 1, the main switch is on until the current reaches the turn off threshold. In cycle 2, the switch is kept off until the turn on threshold is reached. In Figure 9,  $V_{SEN-UPPER_TH}$  and  $V_{SEN-LOWER-TH}$  are assumed to be their typical value of 30 mV.

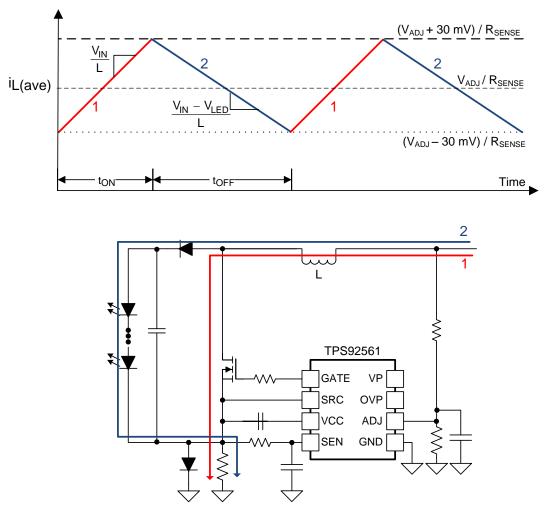
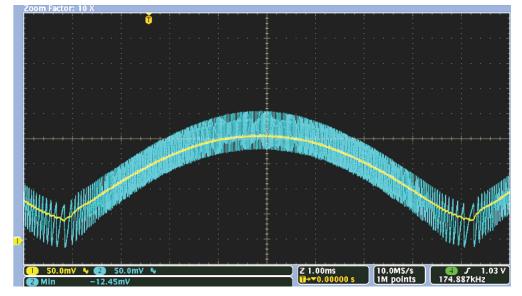


Figure 9. Basics of Hysteretic Boost Operation



### Sample Scope Capture



The main inductor current varies in a window around the ADJ reference voltage:

Figure 10. TPS92561 Operation Waveform (1 ms/div) Yellow: ADJ Voltage (50 mV/div) Blue: R<sub>SENSE</sub> Voltage (50 mV/div)

### VCC Bias Supply and Start-Up

The TPS92561 device can be configured to obtain bias power in several different configurations: AUX winding from the main inductor (see Figure 15), a linear regulator from the input rectified AC (see Figure 16), or a linear regulator from the output LED voltage (see Figure 17). A linear regulator can be constructed from a resistor, a Zener diode, and a N-Channel MOSFET. Each configuration has benefits and trade-offs.

<b>Bias Configuration</b>	Description					
	Highest efficiency bias choice					
Coupled inductor bias with linear regulator start-up	Requires a custom magnetic, which can range in cost similar to an off-the-shelf single coil inductor					
(see Figure 15)	Method to start the TPS92561 device (linear) still required, however, can be undersized for start-up condition only. VCC <sub>UVLO</sub> has not been engineered to support resistive start-up methods.					
	Lowest efficiency bias choice because output voltage is higher than input					
Linear regulator from	Ensures fast output turn off due to bias draining output capacitor					
output	Aids dimming performance under deep dimming, a stable bias is always available					
(see Figure 16)	Lower capacitance value required at VP pin, output capacitor is doubling as VP capacitor					
	Can be supplemented with charge pump bias circuit to achieve higher efficiency					
Linear regulator from input	Better efficiency performance than linear regulator derived from output					
(see Figure 17)	Higher VP capacitor value required					

### **Table 2. VCC Bias Power Configurations**

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### VCC and VP Connection

A bias voltage with a maximum of 42 V is connected to the VP pin to supply the internal 8.3 V (typical) VCC linear regulator. This voltage is also used to drive the main FET gate. Use a FET with a gate threshold at least 750 mV below the VCC voltage. The VCC capacitor ground must be placed at the SEN pin. This ensures the SEN voltage is free of switching spikes that occur at the edge of each switching cycle.

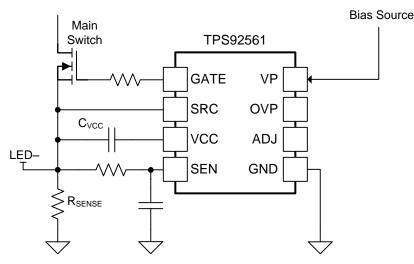


Figure 11. TPS92561 Bias, SRC, and C<sub>VCC</sub> Connection

### Output Current Control (ADJ, SEN)

The TPS92561 power stage design follows two rules:

- 1. Output current is determined by the ADJ reference voltage, the sense resistor selected, and the converter operating points,  $V_{IN}$  and  $V_{LED}$ .
- 2. Output frequency is determined by the inductance value and the SEN pin hysteresis V<sub>SEN</sub>. For off-line applications, the effective hysteresis must be increased using an R-C filter on the SEN pin.

Because the TPS92561 device does not have leading edge blanking, the SEN pin filter must be used to obtain consistent operation. The SEN pin filter is typically set using an R-C with a corner frequency close to the desired switching frequency. Leading edge blanking was not implemented to allow high-frequency operation in other non-off-line applications.

At start up ( $V_{ADJ}$  < 90 mV) a small current is supplied to the  $V_{ADJ}$  divider to ensure a reference is available to begin converter switching. When the ADJ voltage is above 90 mV, the current source is shut off.

### Setting the Output Current

Using the desired ADJ reference voltage, the input current can be calculated based on:

$$I_{in} = \frac{V_{ADJ}}{R_{SENSE}}$$

where  $V_{ADJ}$  can be DC, rectified AC derived, or other source.

(1)

If  $V_{ADJ}$  is derived from a voltage divider from the input rectified AC, we can solve for the R9 resistor divider value based on, for example, a  $V_{ADJ}$  voltage of 150 mV, an R17 value of 374  $\Omega$ , and the average value of the sine wave:

$$R9 = \frac{\left(VIN_{RMS} \times 0.9 \times R17\right)}{V_{ADJ}} - R17$$

(2)

# TPS92561 Rectified GATE VP SRC OVP VCC ADJ SEN GND

Figure 12. TPS92561 ADJ Connection

To find the  $R_{SENSE}$  value, where  $\eta$  is the converter efficiency, assume 0.9.

$$R_{\text{SENSE}} = \frac{V_{\text{IN-RMS}} \times V_{\text{ADJ}} \times \eta}{V_{\text{LED}} \times I_{\text{LED}}}$$

(3)

### Selecting an Inductance

The TPS92561 device is hysteretic. Therefore, switching transitions are based on the sensed current in the inductor. There is no direct control of the switching frequency other then the relationship of the comparator hysteresis to the inductor ripple. A typical switching frequency of an off-line converter using a rectified AC injected reference could vary up to 50 kHz over a line cycle. This creates a spread-spectrum effect and helps reduced conducted EMI.

A typical line injected (using a divided down rectified AC as the reference) hysteretic boost converter reaches the peak switching frequency when  $V_{LED} = 2 \times V_{RECTIFIED AC}$ , or when the duty cycle D = 0.5. We call this operating point  $V_{IN-FSW-PK}$ . Use this voltage as the typical operating point for the design equations. Solve for the  $V_{IN-FSW-PK}$  term based on:

$$\frac{V_{LED}}{V_{IN-FSW-PK}} = \frac{1}{1-D} \quad \text{or} \quad V_{IN-FSW-PK} = \frac{V_{LED}}{2}$$
(4)

Select the approximate highest desired frequency (for example,  $f_{SW-PK}$  of 65 kHz could be used), then design the SEN pin filter with corner frequency equal to  $f_{SW-PK}$ . The filter and the internal hysteresis define the inductor ripple for a given inductance. This has the effect of increasing the SEN pin hysteresis V<sub>SEN-HYS-2</sub> to approximately 140 mV. Select a C12 value between 1000 and 4700 pF. Solve for the resistor R12 in the filter based on:

$$R_{12} = \frac{1}{2\pi \times f_{SW-PK} \times C_{12}}$$
(5)
$$TPS92561$$

$$FED$$

$$FED$$

$$FR_{SENSE}$$

Figure 13. Current Sense

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With the effective hysteresis, calculate the inductor peak-to-peak,  $\Delta i_{L-PP}$  ripple current using:

$$i_{L-PP} = \frac{V_{SEN-HYS-2}}{R_{SENSE}}$$

Λ

To find the converter inductance, L, substitute into:

$$L = \frac{V_{IN-FSW-PK} \times D \times \left(\frac{1}{f_{SW-PK}}\right)}{\Delta i_{L-PP}}$$

To further aid in the converter design, see the TPS92561 design tool, TI literature number SLUC517.

### Important Design Consideration: Diode in Parallel With Sense Resistance

Figure 13 shows a diode in use in parallel with the R<sub>SENSE</sub> resistor. The diode clamps the SEN pin voltage when the boost converter is first powered up. Because a boost converter utilizes a diode connected to the output, the output capacitor is charged immediately when power is applied.

### CAUTION

The current charging the output capacitor when  $V_{\rm IN}$  is applied flows through the sense resistors, and if it is not clamped by the diode, can exceed the TPS92561 SEN pin rating, which may damage the device.

### **Gate Driver Operation**

An additional aid to converter operation and radiated EMI is to slow the main FET switching speed. This can be accomplished by adding a resistor in series with the FET gate. A fast turn off diode across the resistor could also be implemented to improve efficiency. For off-line designs, use a gate resistance value  $\geq$  75  $\Omega$ .

As in all power converters grounding and layout are key considerations. Give careful attention to the layout of the sense resistors, GND pin, VCC, and SRC connections, as well as the FET Gate and Source connections. All should follow short and low-inductance paths. For examples, see the TPS92561 EVM User's Guide, *SLUUAU9*.

### **Overcurrent Protection**

The TPS92561 device inherently limits the main switch current, but cannot implement output short circuit protection because of the converter (boost) topology. To implement LED short-circuit protection in a boost converter requires a blocking switch or other means to open the path to the output, which adds significant cost and complexity to the solution and is not commonly used. An input fuse should be used as output overcurrent protection.

### **Overvoltage Protection (OVP)**

Overvoltage protection is implemented using a resistor voltage divider to the output. Note that the output voltage is high (> 200 V) so the resistor divider should contain a high (> 1 M $\Omega$ ) value. Also use a small cap on OVP.

First pick a value for R18, for example 1.6 M $\Omega$  and select the desired overvoltage protection voltage V<sub>OVP</sub>. Using the V<sub>OVP-UPTH</sub> value (1.19 V, typical) the trip point can then be computed using:

$$R19 = \frac{R18 \times V_{OVP-UPTH}}{V_{OVP} - V_{OVP-UPTH}}$$

(8)

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(6)

(7)



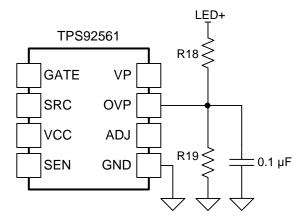


Figure 14. Overvoltage Protection Circuit

When the OVP trip point is reached the converter shuts off until the OVP voltage drops below the level controlled by the OVP hysteresis,  $V_{OVP-HYS}$  (44 mV, typical). After OVP is reached, switching begins again when  $V_{LED}$  falls to the restart voltage (one  $V_{OVP-HYS}$  term ignored):

$$V_{OVP\_RESTART} = V_{OVP} - \left(\frac{V_{OVP\_HYS}}{R19}\right) R18$$
(9)

### **Output Bulk Capacitor**

The required output bulk capacitor,  $C_{\text{BULK}}$ , stores energy during the input voltage zero crossing interval and limits the twice the line frequency ripple component flowing through the LEDs. The following equation describes the calculation of the output capacitor value:

$$C_{\text{BULK}} \geq \frac{P_{\text{IN}}}{4\pi \times f_{\text{L}} \times R_{\text{LED}} \times V_{\text{LED}} \times I_{\text{LED(ripple)}}}$$

where

- R<sub>LED</sub> is the dynamic resistance of LED string
- I<sub>LED(ripple)</sub> is the peak-to-peak LED ripple current
- f<sub>L</sub> is line frequency

(10)

 $R_{LED}$  is found by computing the difference in LED forward voltage divided by the difference in LED current for a given LED using the manufacturer's V<sub>F</sub> versus I<sub>F</sub> curve. For more details, see Application Note 1656.

In typical applications, the solution size becomes a limiting factor and dictates the maximum dimensions of the bulk capacitor. When selecting an electrolytic capacitor, manufacturer recommended de-rating factors should be applied based on the worst case capacitor ripple current, output voltage, and operating temperature to achieve the desired operating lifetime.

### Phase Dimming

After following the design procedure for a TPS92561 non-dimming design, the creation of a TRIAC dimmer compatible design only requires the addition of an input snubber (R-C), as shown in Figure 17. Ideally, a capacitor value of 3x the input filter capacitance would be implemented to ensure sufficient damping of the input filter resonance. However, capacitance values as low as 2x tested successfully. If the input voltage is used to provide the converter reference, dimming occurs naturally with the decreasing ADJ set point and decreased power transfer due to shorter line-cycle conduction times.

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### **Application Circuits**

Target LED lamp applications include:

- A-15, A-19, A-21, A-23
- R-20, R-25, R-27, R-30, R-40
- PS-25, PS-30, PS-35
- BR-30, BR-38, BR-40
- PAR-20, PAR-30, PAR-30L
- MR-16, GU-10
- G-25, G-30, G-40

Applications also include: fluorescent replacement, recessed (canister) type lighting replacement, and new LED-specific lighting form factors.

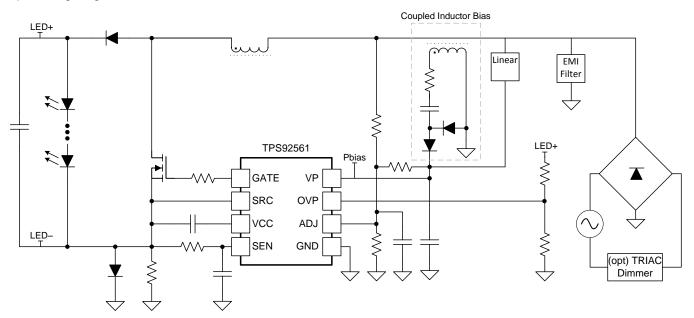
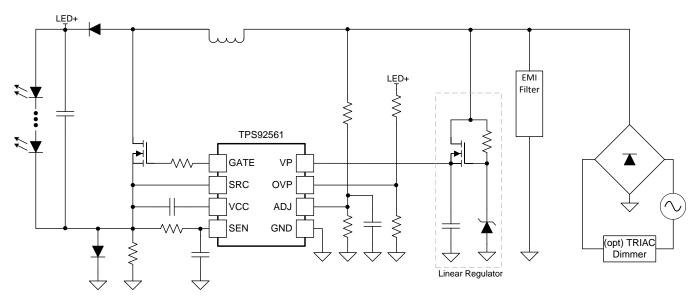
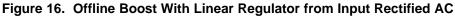


Figure 15. Offline Boost Configuration With Auxiliary Winding and Linear Regulator for Start-Up







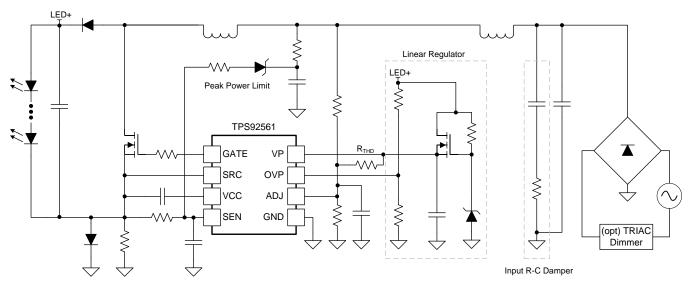


Figure 17. Offline Boost With Linear Regulator from V<sub>LED+</sub>,THD Improvement Resistor, Peak Power Limit Circuit, EMI Filter, and Snubber for TRIAC Dimming

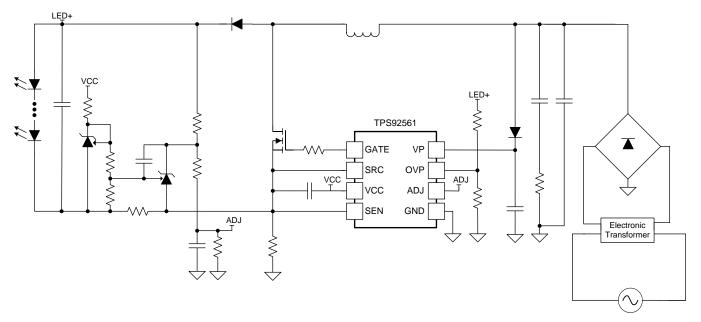


Figure 18. Closed-Loop Regulated E-Transformer Compatible, Non-TRIAC Dimmable Boost for AR111 and MR16 Lamps

## **REVISION HISTORY**

C	hanges from Original (December 2013) to Revision A	Page
•	Updated figure to add AR111 lamps for closed-loop regulated e-transformer compatible, non-TRIAC dimmable boost for AR111 and MR16 lamps	15
C	hanges from Revision A (December 2013) to Revision B	Page
•	Removed product preview banner	1



17-May-2014

## PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TPS92561DGN	ACTIVE	MSOP- PowerPAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	92561	Samples
TPS92561DGNR	ACTIVE	MSOP- PowerPAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	92561	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(<sup>6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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# PACKAGE OPTION ADDENDUM

17-May-2014

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

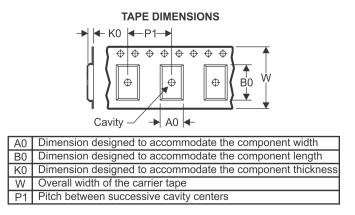
# PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All	dimensions	are	nominal
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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS92561DGNR	MSOP- Power PAD	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

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# PACKAGE MATERIALS INFORMATION

14-Jan-2014



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS92561DGNR	MSOP-PowerPAD	DGN	8	2500	366.0	364.0	50.0

DGN (S-PDSO-G8)

PowerPAD<sup>™</sup> PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

- C. Body dimensions do not include mold flash or protrusion.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="http://www.ti.com">http://www.ti.com</a>.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.

F. Falls within JEDEC MO-187 variation AA-T

PowerPAD is a trademark of Texas Instruments.



# DGN (S-PDSO-G8)

# PowerPAD<sup>™</sup> PLASTIC SMALL OUTLINE

### THERMAL INFORMATION

This PowerPAD  $^{M}$  package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.





4206323-2/1 12/11

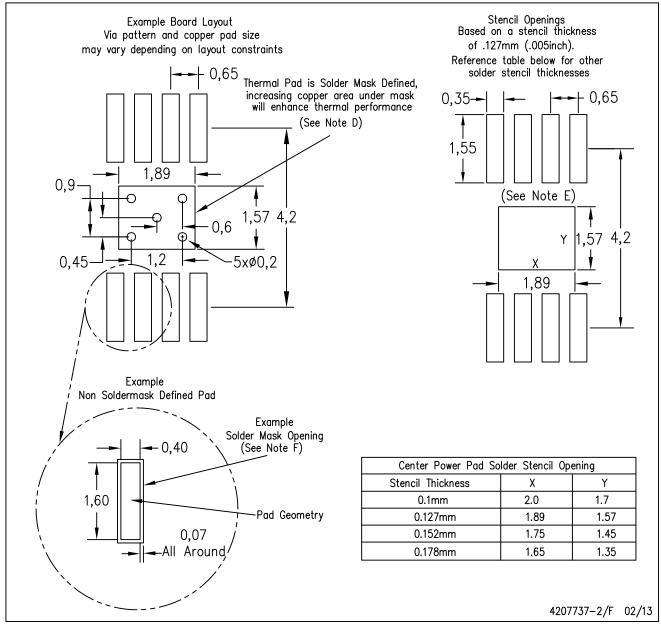
NOTE: All linear dimensions are in millimeters

#### PowerPAD is a trademark of Texas Instruments



# DGN (R-PDSO-G8)

# PowerPAD<sup>™</sup> PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
  - D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>.
  - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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